

## Silicon PNP Power Transistors

## 2SB919

## DESCRIPTION

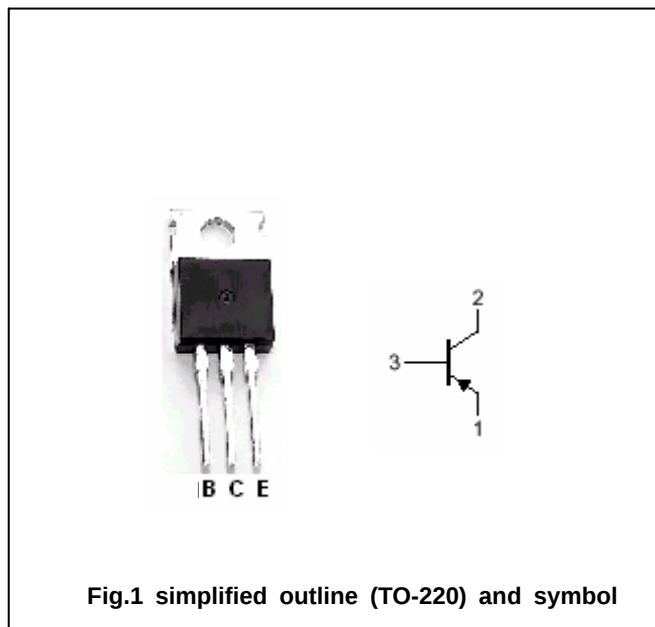
- With TO-220C package
- Complement to type 2SD1235
- Low collector saturation voltage
- Large current capacity

## APPLICATIONS

- Large current switching of relay drivers, high-speed inverters, converters

## PINNING

| PIN | DESCRIPTION                           |
|-----|---------------------------------------|
| 1   | Emitter                               |
| 2   | Collector; connected to mounting base |
| 3   | Base                                  |

Absolute maximum ratings( $T_a=25^\circ\text{C}$ )

| SYMBOL    | PARAMETER                 | CONDITIONS     | VALUE   | UNIT |
|-----------|---------------------------|----------------|---------|------|
| $V_{CBO}$ | Collector-base voltage    | Open emitter   | -60     | V    |
| $V_{CEO}$ | Collector-emitter voltage | Open base      | -30     | V    |
| $V_{EBO}$ | Emitter-base voltage      | Open collector | -6      | V    |
| $I_C$     | Collector current (DC)    |                | -8      | A    |
| $I_{CM}$  | Collector current-Peak    |                | -15     | A    |
| $P_C$     | Collector dissipation     | $T_a=25$       | 1.75    | W    |
|           |                           | $T_C=25$       | 30      |      |
| $T_j$     | Junction temperature      |                | 150     |      |
| $T_{stg}$ | Storage temperature       |                | -50~150 |      |

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## CHARACTERISTICS

Tj=25 unless otherwise specified

| SYMBOL        | PARAMETER                            | CONDITIONS                       | MIN | TYP. | MAX  | UNIT |
|---------------|--------------------------------------|----------------------------------|-----|------|------|------|
| $V_{(BR)CEO}$ | Collector-emitter breakdown voltage  | $I_C = -1mA$ ; $R_{BE} = \infty$ | -30 |      |      | V    |
| $V_{(BR)CBO}$ | Collector-base breakdown voltage     | $I_C = -1mA$ ; $I_E = 0$         | -60 |      |      | V    |
| $V_{(BR)EBO}$ | Emitter-base breakdown voltage       | $I_E = -1mA$ ; $I_C = 0$         | -6  |      |      | V    |
| $V_{CEsat}$   | Collector-emitter saturation voltage | $I_C = -3A$ ; $I_B = -0.15A$     |     |      | -0.5 | V    |
| $I_{CBO}$     | Collector cut-off current            | $V_{CB} = -40V$ ; $I_E = 0$      |     |      | -0.1 | mA   |
| $I_{EBO}$     | Emitter cut-off current              | $V_{EB} = -4V$ ; $I_C = 0$       |     |      | -0.1 | mA   |
| $h_{FE-1}$    | DC current gain                      | $I_C = -1A$ ; $V_{CE} = -2V$     | 70  |      | 280  |      |
| $h_{FE-2}$    | DC current gain                      | $I_C = -4A$ ; $V_{CE} = -2V$     | 30  |      |      |      |
| $f_T$         | Transition frequency                 | $I_C = -1A$ ; $V_{CE} = -5V$     |     | 120  |      | MHz  |

## Switching times

|           |               |                                                                                 |  |      |  |         |
|-----------|---------------|---------------------------------------------------------------------------------|--|------|--|---------|
| $t_{on}$  | Turn-on time  | $I_C = -4A$ ; $V_{CC} = -10V$<br>$I_{B1} = -I_{B2} = -0.2A$ ; $R_L = 2.5\Omega$ |  | 0.1  |  | $\mu s$ |
| $t_{stg}$ | Storage time  |                                                                                 |  | 0.2  |  | $\mu s$ |
| $t_f$     | Turn-off time |                                                                                 |  | 0.03 |  | $\mu s$ |

◆  $h_{FE-1}$  Classifications

| Q      | R       | S       |
|--------|---------|---------|
| 70-140 | 100-200 | 140-280 |

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## PACKAGE OUTLINE

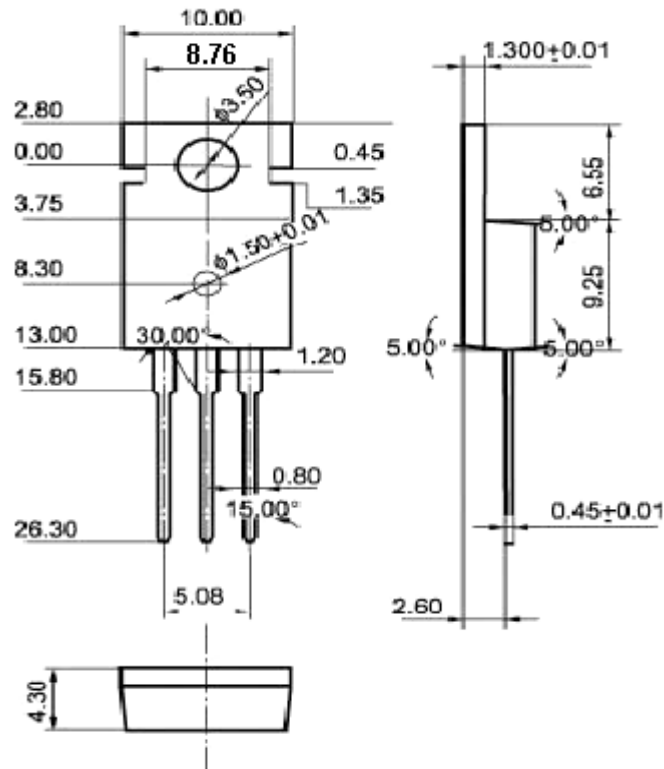


Fig.2 Outline dimensions (unindicated tolerance: ± 0.10mm)

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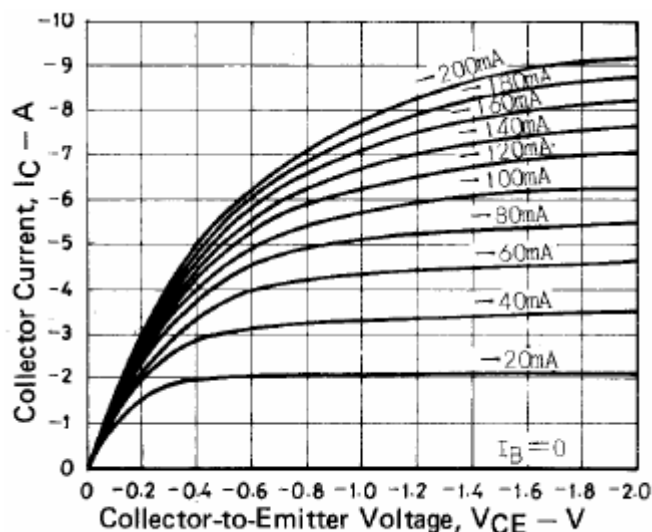


Fig.3 Static Characteristic

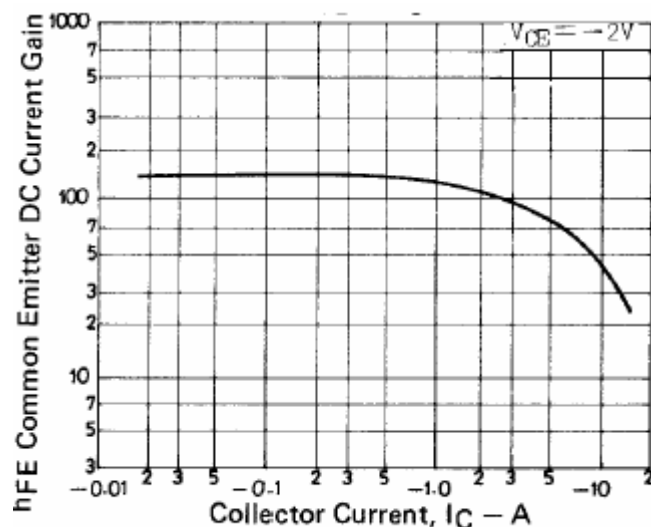


Fig.4 DC current Gain

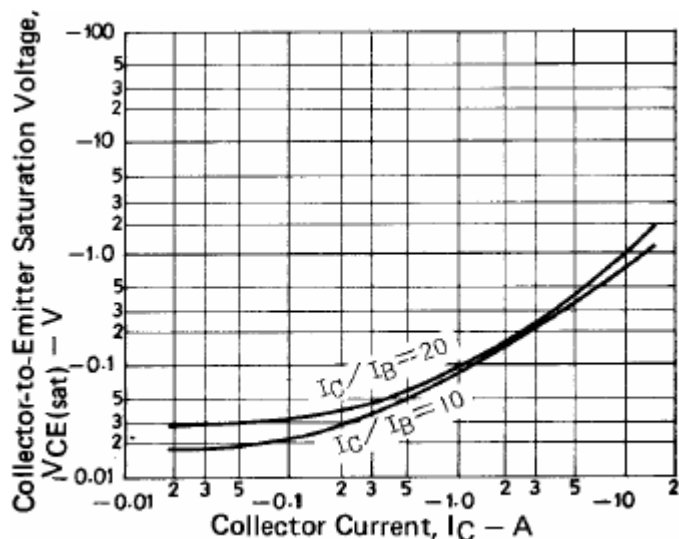


Fig.5 Collector-Emitter Saturation Voltage

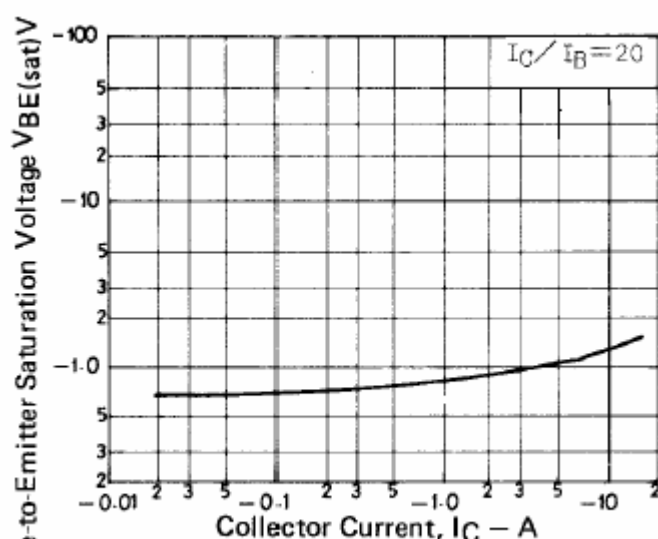


Fig.6 Base-Emitter Saturation Voltage

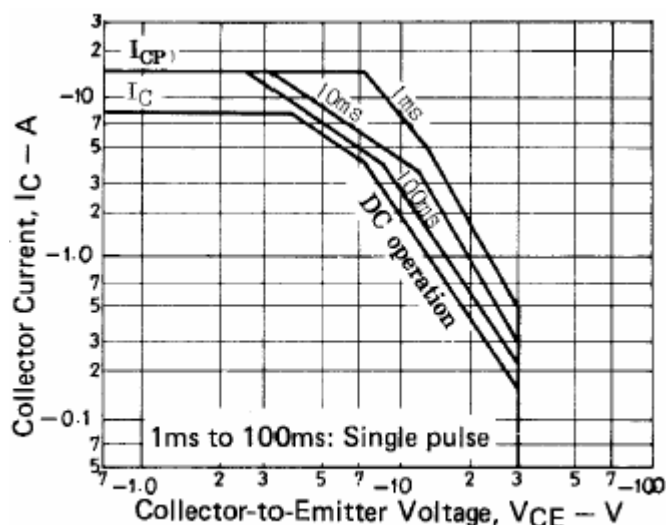


Fig.7 Safe Operating Area